AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A sputtering target comprising:

a material containing silicon carbide and silicon

wherein a volume ratio of the silicon carbide ranges from about 50% to about 70% when a volume ratio of silicon carbide equals the entire volume of silicon carbide/(the entire volume of silicon carbide + the entire volume of silicon) × 100;

wherein the silicon carbide is a powder comprising a mixture of a silicon carbide powder having a most frequent grains of about 1.7 to about 2.7 μm and a silicon carbide powder having most frequent grains of about 10.5 to about 21.5 μm.

2. (Original) The sputtering target as claimed in claim 1 wherein the volume ratio of the silicon carbide is about 55% to about 65%.

3. (Previously Presented) The sputtering target as claimed in claim 1, wherein the material containing silicon carbide and silicon is prepared by a reaction sintering method.

4. (Previously Presented) The sputtering target as claimed in claim 1, wherein a weight ratio of impurities contained in the silicon is about 0.01% or less.

5. (Previously Presented) The sputtering target as claimed in claim 1, wherein a volume resistivity of a covering layer formed on a glass plate is about 3.0×10^3 ($\Omega \cdot$ cm) or less.

6. (Cancelled).

7. (Currently Amended) A method for manufacturing a sputtering target comprising:

dispersing a silicon carbide powder comprising a mixture of a silicon carbide powder having a most frequent grains of about 1.7 to about 2.7 μm and a silicon carbide powder having most frequent grains of about 10.5 to about 21.5 μm, and a carbon source, into a solvent to provide a mixed powder in a slurry ~~form,~~form;

pouring the resulting mixed powder into a mold and drying the same to obtain a green ~~material,~~ material;

calcinating the resulting green material at about 1200 to about 1800°C under a vacuum or inert gas atmosphere to obtain a calcined ~~material,~~ material; and

impregnating the resulting calcined material with molten metallic silicon by capillary action to react free carbon in the calcined material with the silicon aspirated into the calcined material due to the capillary action phenomenon thereby obtaining a silicon carbide material.

8. (Previously Presented) The sputtering target as claimed in claim 1, wherein the refractive indexes of covering layers formed on glass plates at the measured optical wavelength of 633 nm are 4.16 or less.

9. (New) The sputtering target as claimed in claim 1, wherein the volume ratio of silicon carbide is about 50%, and the silicon carbide sintered material is obtained through mixing a silicon carbide powder having 2.3 μm diameter and a silicon carbide powder having 16.4 μm diameter in a volume ratio equal to 50/50.

10. (New) The sputtering target as claimed in claim 1, wherein the volume ratio of silicon carbide is about 70%, and the silicon carbide sintered material is obtained through mixing a silicon carbide powder having 2.3 μm diameter and a silicon carbide powder having 16.4 μm diameter in a volume ratio equal to 70/30.

11. (New) The method for manufacturing a sputtering target as claimed in claim 7, wherein the volume ratio of the mixture of silicon carbide powder having 2.3 μm diameter and the silicon carbide powder having 16.4 μm diameter is equal to 50/50.

12. (New) The method for manufacturing a sputtering target as claimed in claim 7, wherein the volume ratio of the mixture of silicon carbide powder having 2.3 μm diameter and the silicon carbide powder having 16.4 μm diameter is equal to 70/30.